

ABSTRACT

CMP slurries for oxide film and a method for forming a metal line contact plug of a semiconductor device are described herein. When a polishing process of a multi-layer film is performed by using the disclosed CMP slurry for oxide film including an HXO_n compound (wherein n is an integer from 1 to 4), a stable landing plug poly can be formed by preventing step differences by reducing interlayer polishing speed differences.